

74HC2G125-Q100; 74HCT2G125-Q100

Dual buffer/line driver; 3-state

Rev. 1 — 3 April 2013

Product data sheet

1. General description

The 74HC2G125-Q100; 74HCT2G125-Q100 are dual buffer/line drivers with 3-state outputs controlled by the output enable inputs ($\overline{\text{nOE}}$). Inputs include clamp diodes which enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Input levels:
 - ◆ For 74HC2G125-Q100: CMOS level
 - ◆ For 74HCT2G125-Q100: TTL level
- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power consumption
- Balanced propagation delays
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Multiple package options



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC2G125DP-Q100 74HCT2G125DP-Q100	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HC2G125DC-Q100 74HCT2G125DC-Q100	−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1

4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74HC2G125DP-Q100	H25
74HCT2G125DP-Q100	T25
74HC2G125DC-Q100	H25
74HCT2G125DC-Q100	T25

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

Fig 1. Logic symbol

Fig 2. IEC logic symbol

Fig 3. Logic diagram (one driver)

6. Pinning information

6.1 Pinning

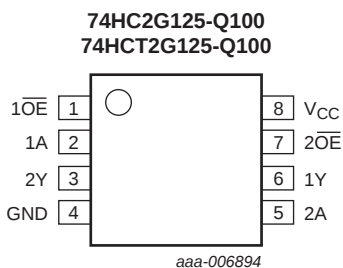


Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1OE, 2OE	1, 7	output enable input (active LOW)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Control	Input	Output
nOE	nA	nY
L	L	L
L	H	H
H	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	^[1] -	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	^[1] -	±20	mA
I _O	output current	V _O = -0.5 V to (V _{CC} + 0.5 V)	^[1] -	35	mA
I _{CC}	supply current		-	70	mA

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
I_{GND}	ground current		-70	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{\text{amb}} = -40\text{ °C to }+125\text{ °C}$	[2]	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC2G125-Q100			74HCT2G125-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_{I}	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_{O}	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{\text{CC}} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{\text{CC}} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{\text{CC}} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristicsVoltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{\text{amb}} = 25\text{ °C}$.

Symbol	Parameter	Conditions	T _{amb} = −40 °C to +85 °C			T _{amb} = −40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HC2G125-Q100								
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = −20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	V
		I _O = −20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	V
		I _O = −20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	V
		I _O = −6.0 mA; V _{CC} = 4.5 V	3.84	4.32	-	3.7	-	V
		I _O = −7.8 mA; V _{CC} = 6.0 V	5.34	5.81	-	5.2	-	V

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	$T_{amb} = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$			$T_{amb} = -40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$		Unit
			Min	Typ	Max	Min	Max	
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 2.0\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 6.0\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 6.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	0.15	0.33	-	0.4	V
		$I_O = 7.8\text{ mA}$; $V_{CC} = 6.0\text{ V}$	-	0.16	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0\text{ V}$	-	-	± 1.0	-	± 1.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0\text{ V}$	-	-	± 5.0	-	± 10	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 6.0\text{ V}$	-	-	10	-	20	μA
C_I	input capacitance		-	1.0	-	-	-	pF
C_O	output capacitance		-	1.5	-	-	-	pF
74HCT2G125-Q100								
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5\text{ V}$ to 5.5 V	2.0	1.6	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5\text{ V}$ to 5.5 V	-	1.2	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5\text{ V}$						
		$I_O = -20\text{ }\mu\text{A}$	4.4	4.5	-	4.4	-	V
		$I_O = -6.0\text{ mA}$	3.84	4.32	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5\text{ V}$						
		$I_O = 20\text{ }\mu\text{A}$	-	0	0.1	-	0.1	V
		$I_O = 6.0\text{ mA}$	-	0.16	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	± 1.0	-	± 1.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	± 5.0	-	± 10	
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 5.5\text{ V}$	-	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5\text{ V}$ to 5.5 V ; $V_I = V_{CC} - 2.1\text{ V}$; $I_O = 0\text{ A}$	-	-	375	-	410	μA
C_I	input capacitance		-	1.0	-	-	-	pF
C_O	output capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 7](#).

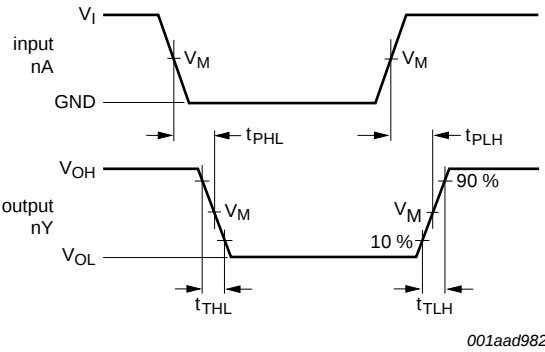
Symbol	Parameter	Conditions	T _{amb} = −40 °C to +85 °C			T _{amb} = −40 °C to +125 °C		Unit	
			Min	Typ ^[1]	Max	Min	Max		
74HC2G125-Q100									
t _{pd}	propagation delay	nA to nY; see Figure 5	[2]						
		V _{CC} = 2.0 V	-	35	115	-	135	ns	
		V _{CC} = 4.5 V	-	11	23	-	27	ns	
		V _{CC} = 5.0 V; C _L = 15 pF	-	10	-	-	-	ns	
		V _{CC} = 6.0 V	-	8	20	-	23	ns	
t _{en}	enable time	n $\overline{\text{OE}}$ to nY; see Figure 6	[2]						
		V _{CC} = 2.0 V	-	40	115	-	135	ns	
		V _{CC} = 4.5 V	-	11	23	-	27	ns	
		V _{CC} = 6.0 V	-	8	20	-	23	ns	
t _{dis}	disable time	n $\overline{\text{OE}}$ to nY; see Figure 6	[2]						
		V _{CC} = 2.0 V	-	24	125	-	150	ns	
		V _{CC} = 4.5 V	-	12	25	-	30	ns	
		V _{CC} = 6.0 V	-	10	21	-	26	ns	
t _t	transition time	see Figure 5	[2]						
		V _{CC} = 2.0 V	-	18	75	-	90	ns	
		V _{CC} = 4.5 V	-	6	15	-	18	ns	
		V _{CC} = 6.0 V	-	5	13	-	15	ns	
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC}	[3]						
		output enabled	-	11	-	-	-	pF	
		output disabled	-	1	-	-	-	pF	
74HCT2G125-Q100									
t _{pd}	propagation delay	nA to nY; see Figure 5	[2]						
		V _{CC} = 4.5 V	-	15	31	-	38	ns	
		V _{CC} = 5.0 V; C _L = 15 pF	-	12	-	-	-	ns	
t _{en}	enable time	n $\overline{\text{OE}}$ to nY; see Figure 6 ; V _{CC} = 4.5 V	[2]	-	15	35	-	42	ns
t _{dis}	disable time	n $\overline{\text{OE}}$ to nY; see Figure 6 ; V _{CC} = 4.5 V	[2]	-	15	31	-	38	ns
t _t	transition time	see Figure 5 ; V _{CC} = 4.5 V	[2]	-	6	15	-	18	ns

Table 8. Dynamic characteristics ...continued
Voltages are referenced to GND (ground = 0 V); $C_L = 50\text{ pF}$ unless otherwise specified; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC} - 1.5 V						
		output enabled	-	11	-	-	-	pF
		output disabled	-	1	-	-	-	pF

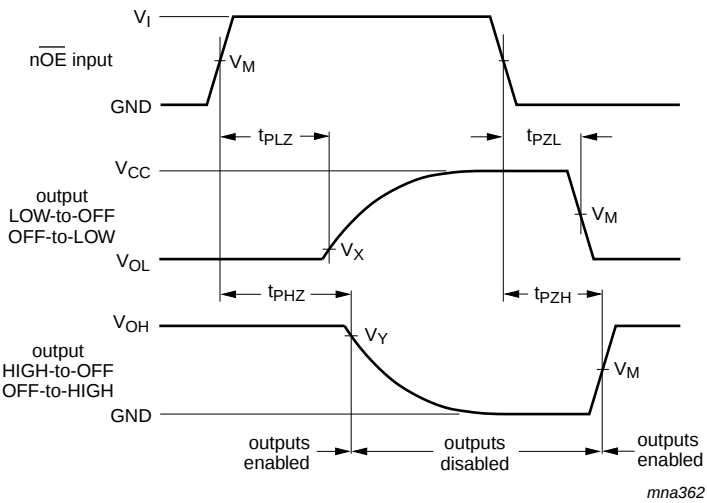
- [1] All typical values are measured at T_{amb} = 25 °C.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
t_{en} is the same as t_{PZL} and t_{PZH}.
t_{dis} is the same as t_{PLZ} and t_{PHZ}.
t_t is the same as t_{THL} and t_{TLH}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



Measurement points are given in [Table 9](#).
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. Propagation delays data input (nA) to output (nY)



Measurement points are given in [Table 9](#).
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. Enable and disable times

Table 9. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC2G125-Q100	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$
74HCT2G125-Q100	1.3 V	1.3 V	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$

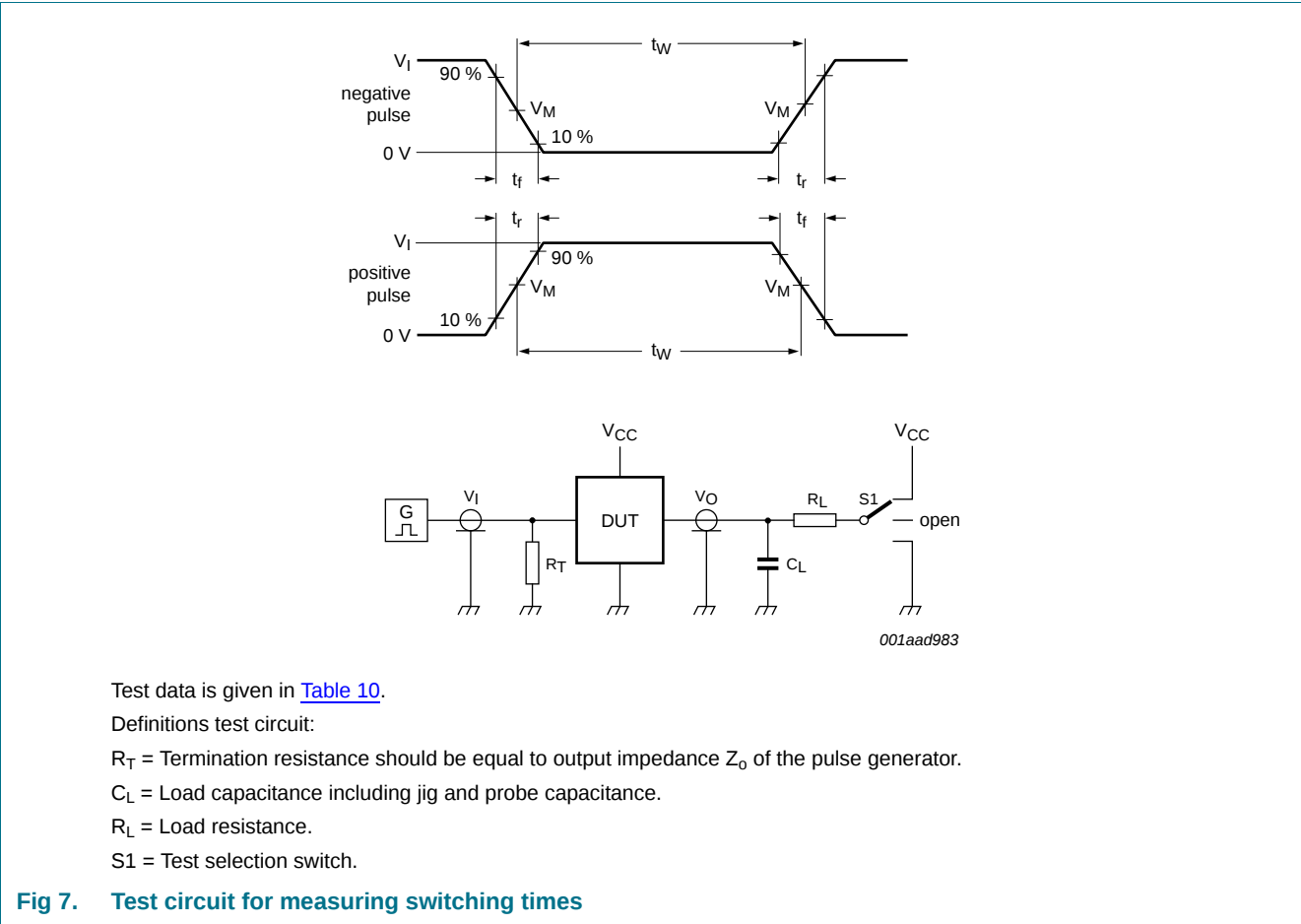


Table 10. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC2G125-Q100	V_{CC}	≤ 6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT2G125-Q100	3 V	≤ 6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

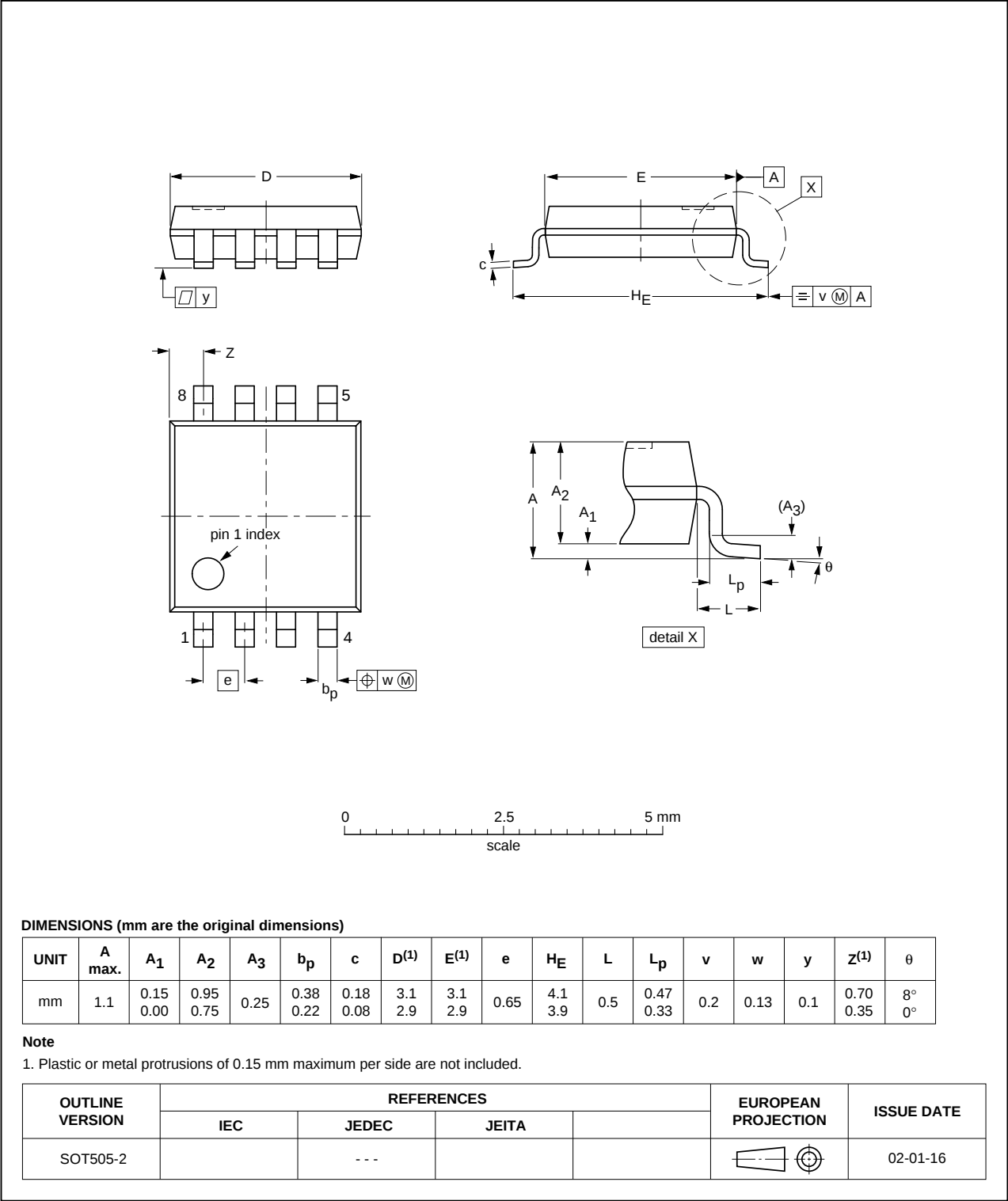


Fig 8. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

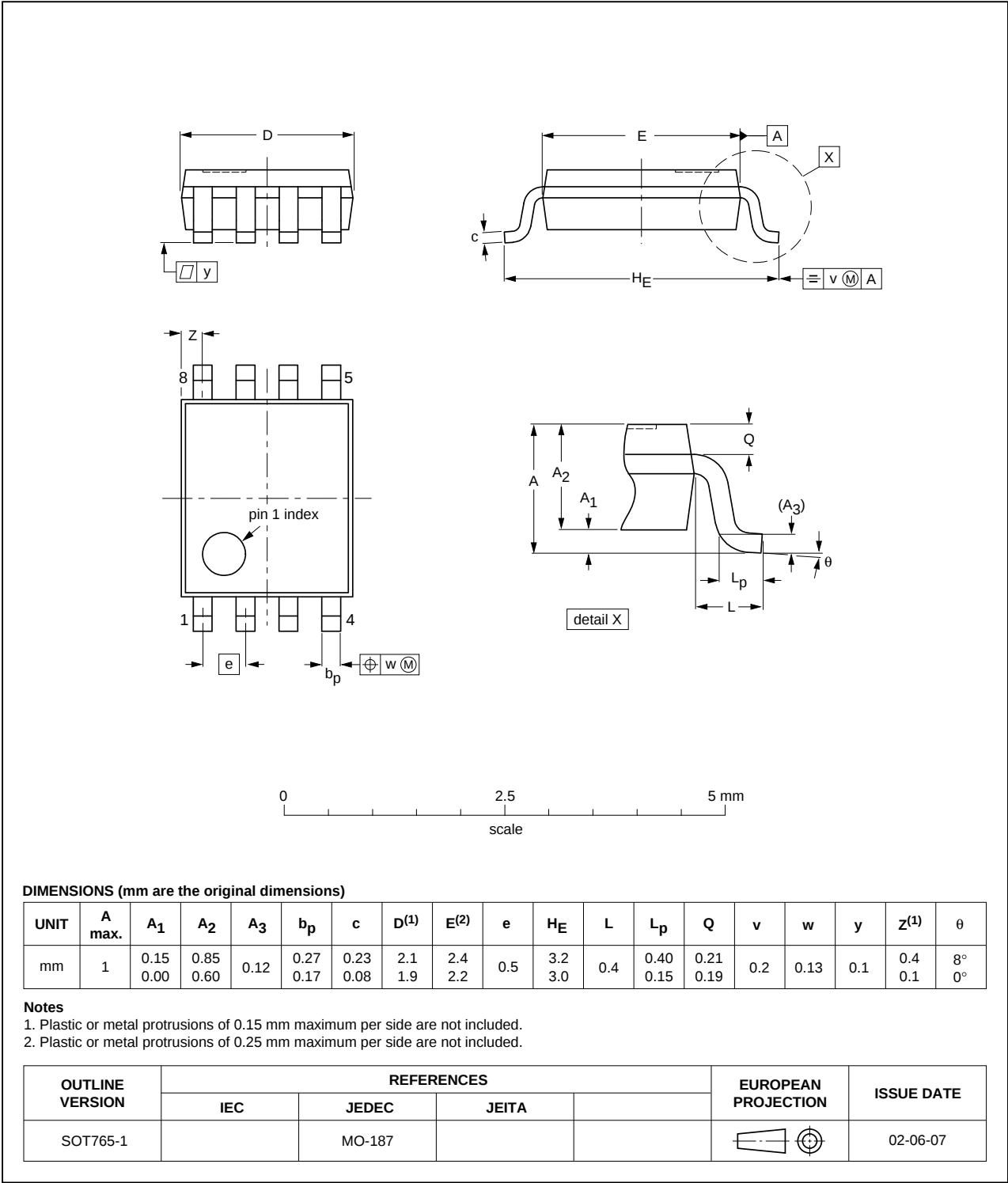


Fig 9. Package outline SOT765-1 (VSSOP8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G125_Q100 v.1	20130403	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9